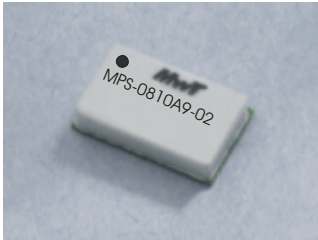


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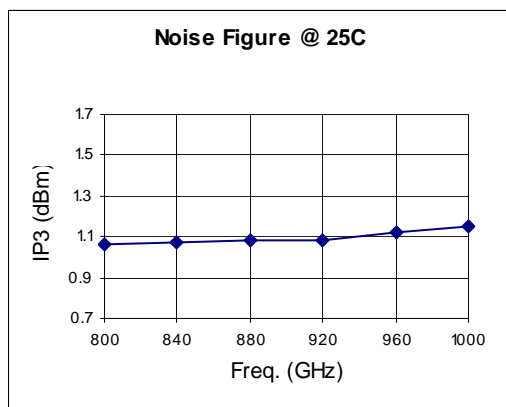


- 1.1 dB NF
- 15.0 dB Gain
- +20.5 dBm P1dB
- 34 dBm IP3
- Single Positive Bias
- Leadless Surface Mount Package

The MPS-0810A9-02 is a low-noise, high dynamic range amplifier designed for ultra linear GSM, TDMA, CDMA, NMT-900 and ETACS receiver applications. The circuit is matched to 50 ohm and employs a single stage GaAs FET with internal matching to provide an exceptional noise figure, 1.1 dB, combined with a high IP3, +34 dBm. Typical applications are cellular base station receivers, tower mounted LNA's, picocell repeaters and receiver multi-couplers.

Electrical Specifications @ 25°C, V_{dd} = 6.0 V, Z_o = 50 ohms

SYMBOL	PARAMETERS	Min	Typical	Max	Unit
Freq	Frequency Range	800		960	MHz
SSG	Small Signal Gain	14.0	15.0		dB
P1 dB	Pout at 1 dB Comp Point		+20.5		dBm
IP3	Third-Order Intercept		34.0		dBm
NF	Noise Figure		1.1	1.5	dB
VSWR	VSWR (Input/Output)		1.5:1	2.0:1	
GOF	Gain Var. over 40 MHz		± 0.2	± 0.5	dB
GOT	Gain Var. over Temp		-0.015		dB/°C
I _{dd}	DC Current		160	240	mA

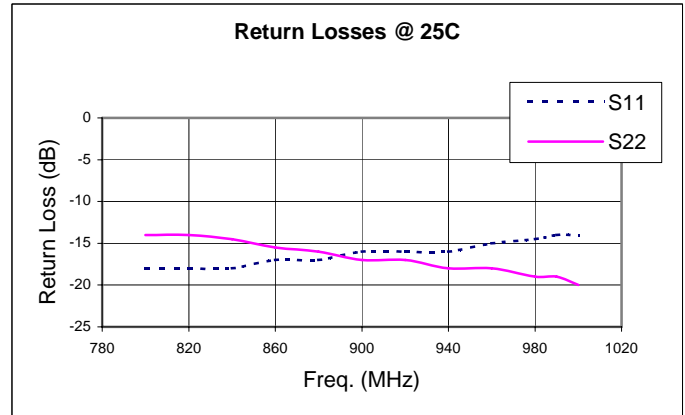
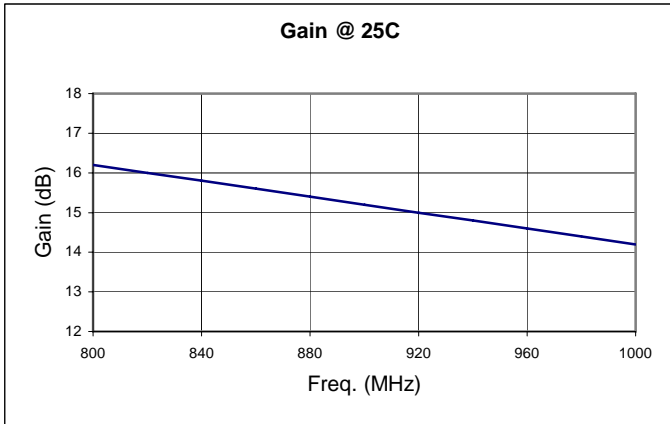


Absolute Maximum Ratings

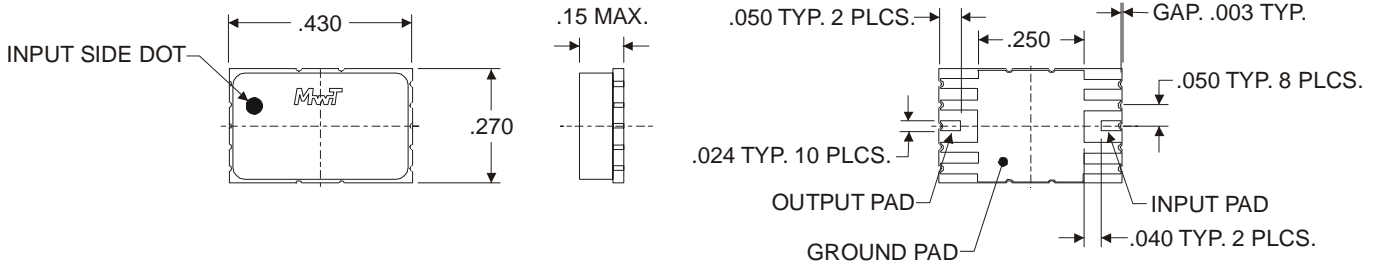
Maximum Bias Voltage	7.0 V
Maximum Continuous RF Input Power	+25 dBm
Maximum Peak Input Power	+27 dBm
Maximum Case Operating Temperature	+85 °C
Maximum Storage Temperature	- 65 to + 150 °C

MicroWave Technology, Inc. an IXYS Company, 4268 Solar Way, Fremont, CA 94538
 510-651-6700 FAX 510-651-2208 EMAIL info@mwttinc.com

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Outline Diagram



Application Circuit

